



FX401

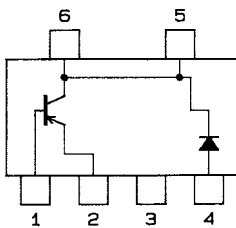
TR:PNP Epitaxial Planar Silicon Transistor
SBD:Schottky Barrier Diode

DC-DC Converter

Features

- Complex type of a low saturation voltage, high speed switching and large current PNP transistor and a fast recovery and low forward voltage Schottky barrier diode facilitating high-density mounting,
- The FX401 is composed on 2chips, one being equivalent to the 2SB1121 and the other the SB30-03P, placed in one package.

Electrical Connection



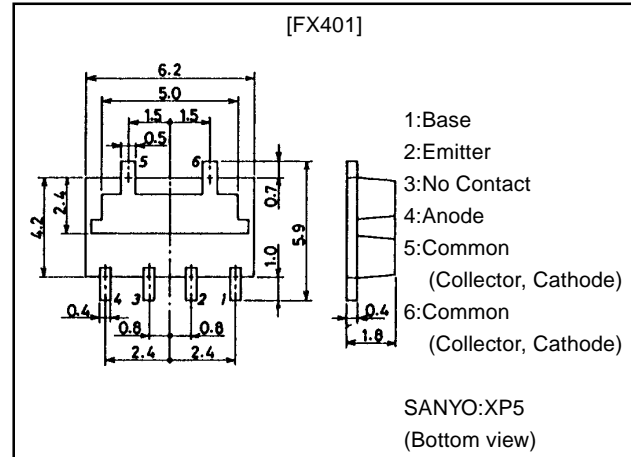
- 1:Base
- 2:Emitter
- 3:No Contact
- 4:Anode
- 5, 6:Common
(Collector, Cathode)

(Top view)

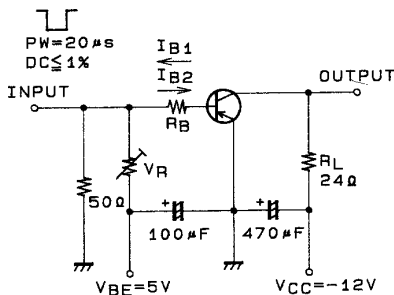
Package Dimensions

unit:mm

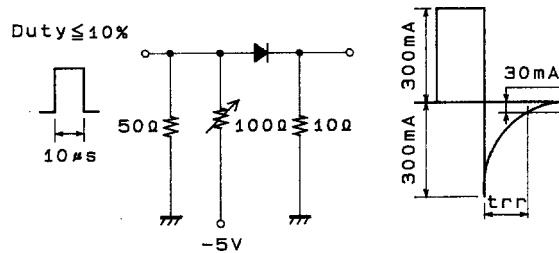
2123



Switching Time Test Circuit



Trr Test Circuit



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
[TR]				
Collector-to-Base Voltage	V_{CBO}		-30	V
Collector-to-Emitter Voltage	V_{CEO}		-25	V
Emitter-to-Base Voltage	V_{EBO}		-6	V
Collector Current	I_C		-2	A
Collector Current (Pulse)	I_{CP}		-5	A
Base Current	I_B		-400	mA
Collector Dissipation	P_C	Mounted on ceramic board (750mm ² ×0.8mm)	1.5	W
Junction Temperature	T_J		150	°C
[SBD]				
Repetitive Peak Reverse Voltage	V_{RRM}		30	V
Non-repetitive Peak Reverse Surge Voltage	V_{RSM}		35	V
Average Rectified Current	I_O		3	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1cycle	10	A
Junction Temperature	T_J		-55 to +125	°C
Storage Temperature	T_{stg}		-55 to +125	°C

· Marking:401

Continued on next page.

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52098HA (KT)/41095TS (KOTO) TA-0087 No.5028-1/4

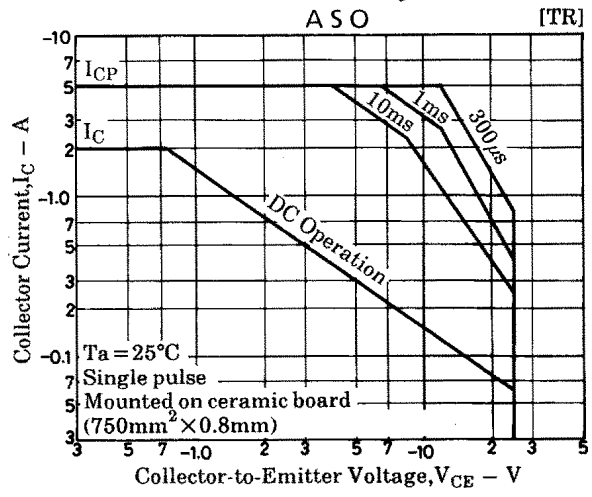
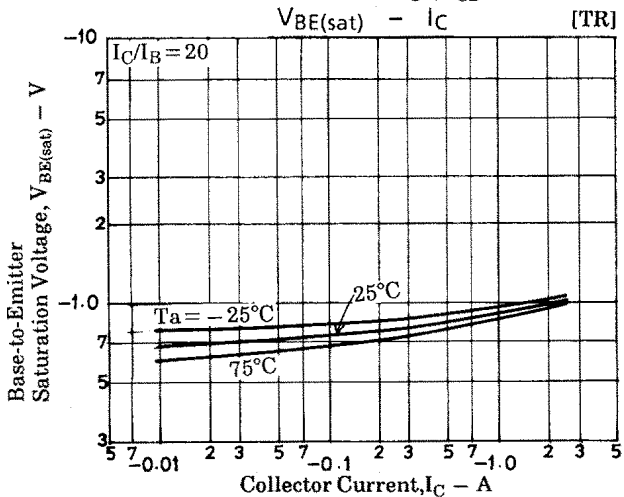
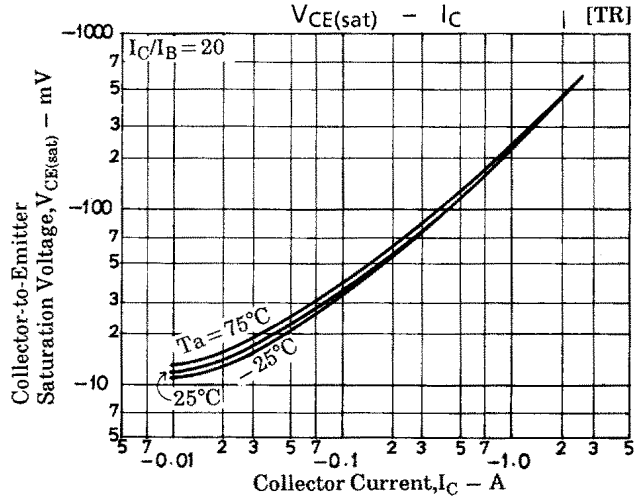
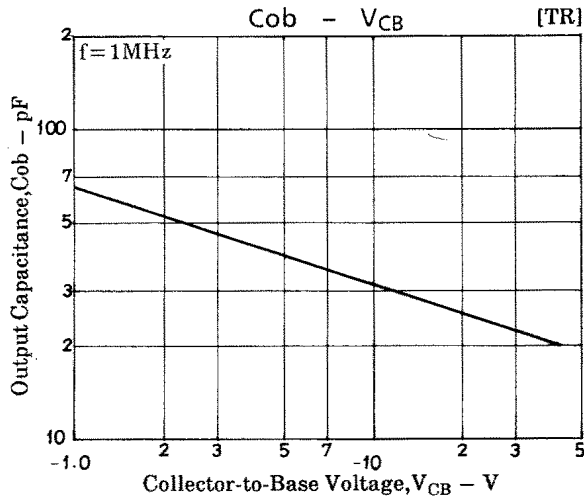
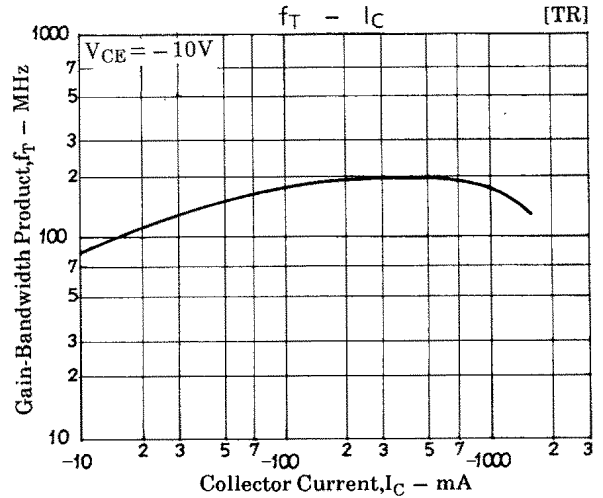
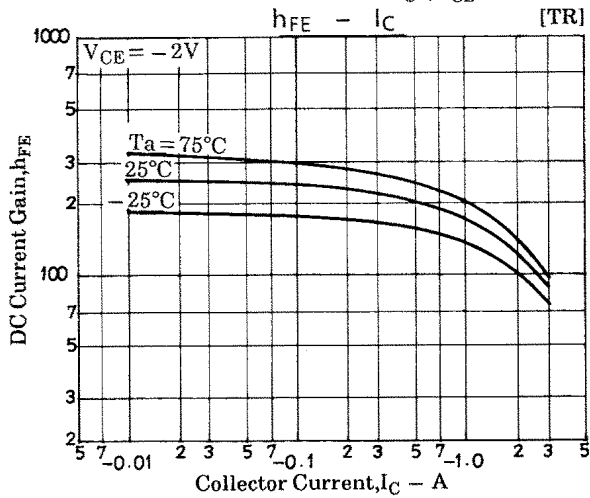
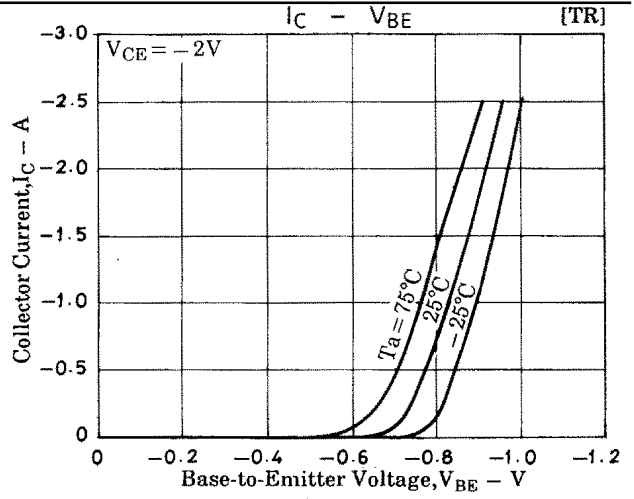
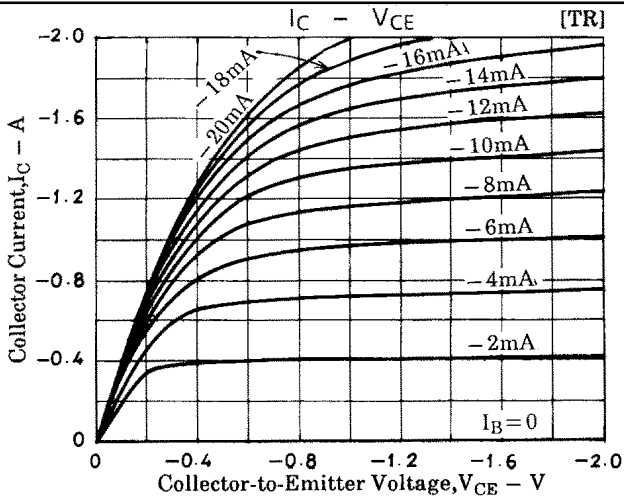
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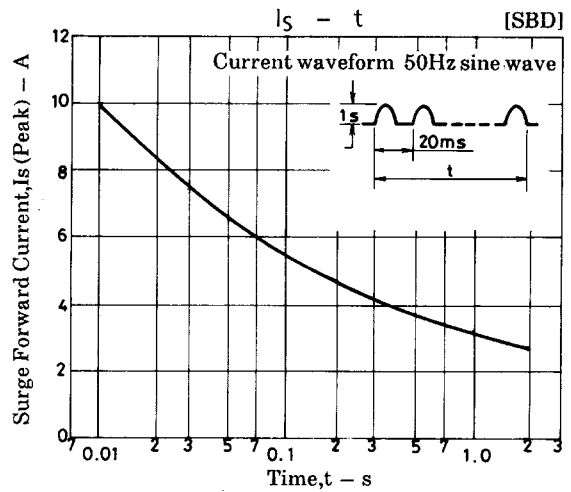
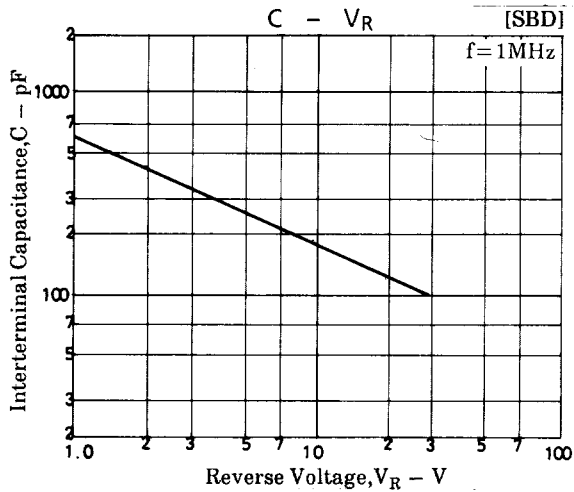
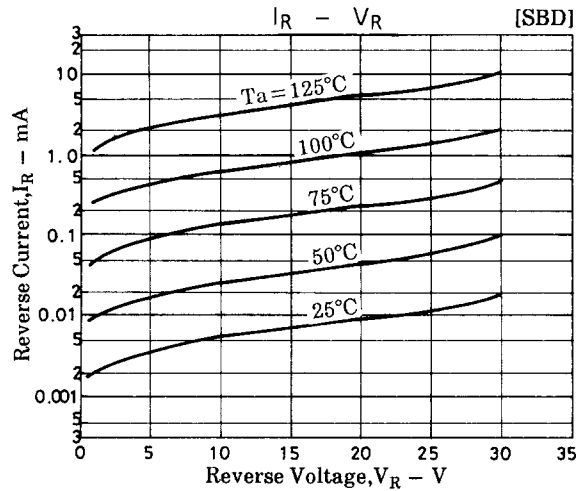
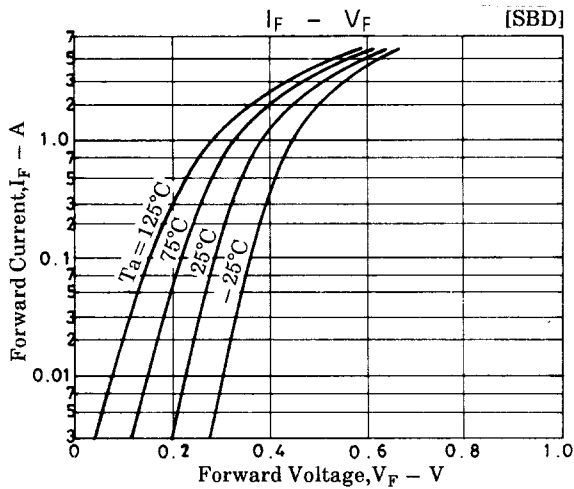
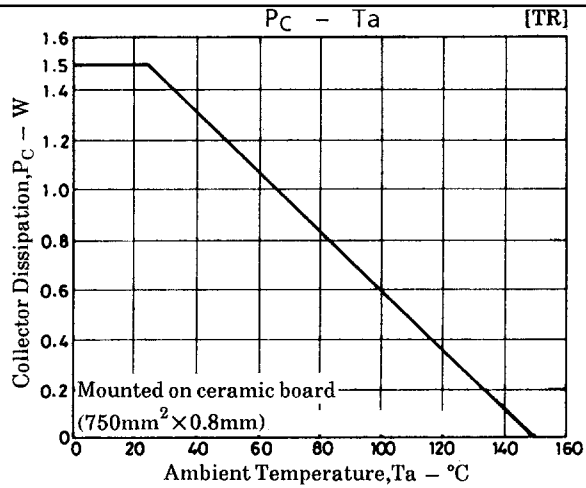
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[TR]						
Collector Cutoff Current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=-2V, I_C=-100mA$	140		400	
	h_{FE2}	$V_{CE}=-2V, I_C=-1.5A$	65			
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-200mA$		320		MHz
Output Capacitance	Cob	$V_{CE}=-10V, f=1MHz$		32		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-75mA$		-350	-600	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=-1.5A, I_B=-75mA$		-1.0	-1.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-30			V
C-E Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, R_{BE}=\infty$	-25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-6			V
Turn-ON Time	t_{on}	See sepcified Test Circuit		60		ns
Storage Time	tstg	See sepcified Test Circuit		350		ns
Fall Time	t_f	See sepcified Test Circuit		25		ns
[SBD] (Value per element)						
Reverse Voltage	V_R	$I_R=1mA$	30			V
Forward Voltage	V_F	$I_F=3A$			0.55	V
Reverse Current	I_R	$V_R=15V$			200	μA
Interterminal Capacitance	C	$V_R=10V, f=1MHz$		160		pF
Reverse Recovery Time	trr	$I_F=I_R=300mA$, See specified Test Circuit			30	ns
Thermal Resistance	Rthj-a	Mounted on ceramic board (750mm ² ×0.8mm)		85		°C/W

FX401



FX401



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